

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(first near float\$3 near gate near (dielectric oxide insulat\$3)) with (second near float\$3 near gate near (dielectric oxide insulat\$3)) with (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:18
L2	8	(first near float\$3 near gate near (dielectric oxide insulat\$3)) with (second near float\$3 near gate near (dielectric oxide insulat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:13
L3	22	(first near float\$3 near gate near (dielectric oxide insulat\$3)) and (second near float\$3 near gate near (dielectric oxide insulat\$3)) and (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:15
L4	871	(first near gate near (dielectric oxide insulat\$3)) with (second near gate near (dielectric oxide insulat\$3)) with (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:18
L5	438	4 and ((float\$3 control) adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:18
L6	305	5 and (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:19
L7	266	6 and thick\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/20 18:20